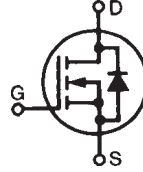


PolarHV™ HiperFET Power MOSFET

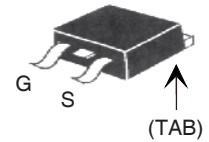
IXFA14N60P
IXFP14N60P
IXFH14N60P

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

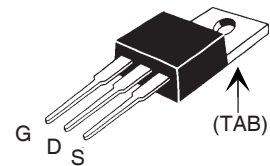


$V_{DSS} = 600V$
 $I_{D25} = 14A$
 $R_{DS(on)} \leq 550m\Omega$
 $t_{rr} \leq 200ns$

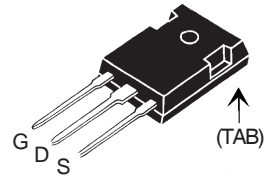
TO-263



TO-220



TO-247



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$ $R_{GS} = 1M\Omega$	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	14	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	42	A
I_A	$T_C = 25^\circ C$	14	A
E_{AS}	$T_C = 25^\circ C$	900	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	300	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nmlb.in.
F_c	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5mA$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V$ $T_J = 125^\circ C$			500 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1	450	550	m Ω

Features

- International standard packages
- Avalanche rated

Advantages

- Easy to mount
- Space savings
- High power density

Applications:

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor drives
- Robotics and servo controls

Fig. 1. Output Characteristics @ 25°C

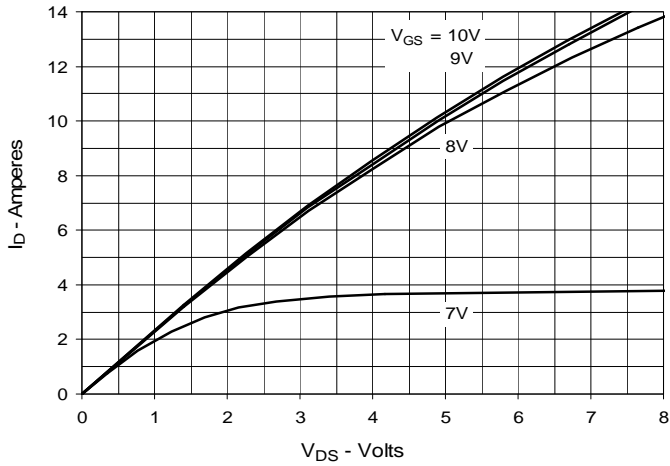


Fig. 2. Extended Output Characteristics @ 25°C

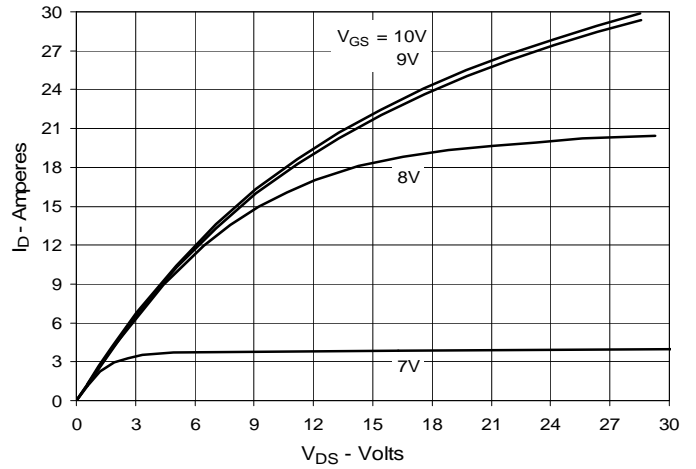


Fig. 3. Output Characteristics @ 125°C

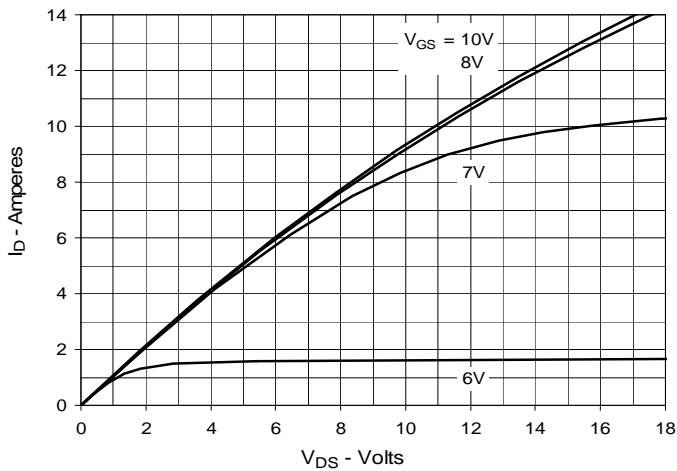


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 7A$ Value vs. Junction Temperature

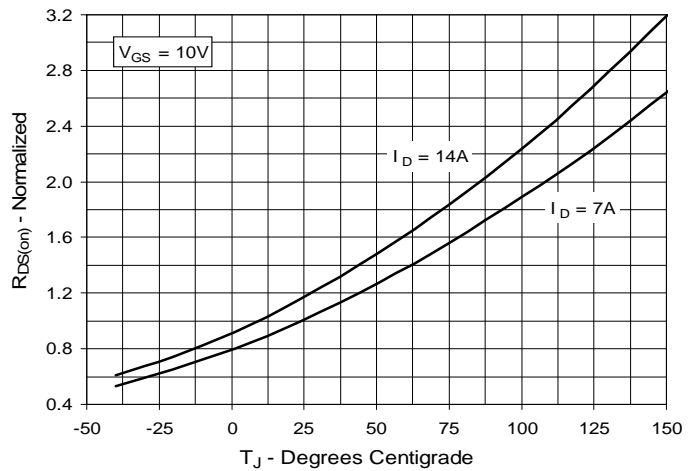


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 7A$ Value vs. Drain Current

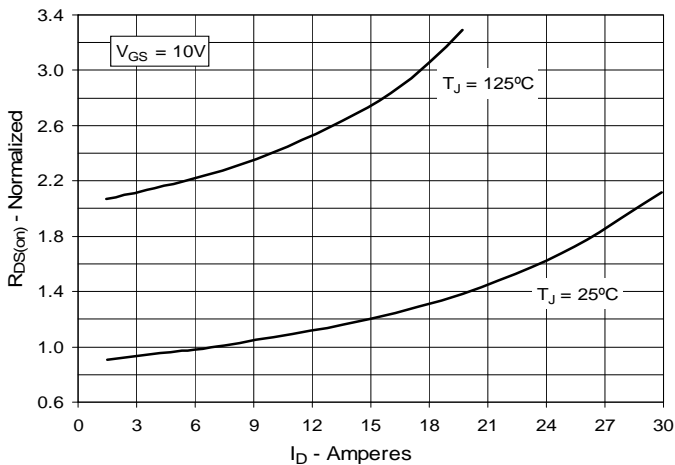


Fig. 6. Maximum Drain Current vs. Case Temperature

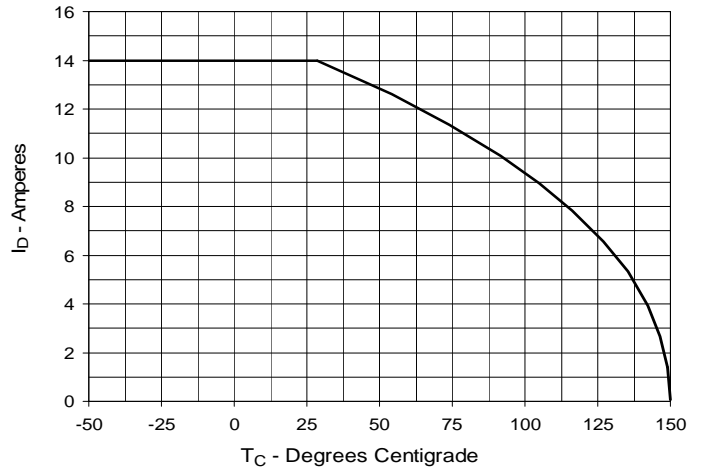


Fig. 7. Input Admittance

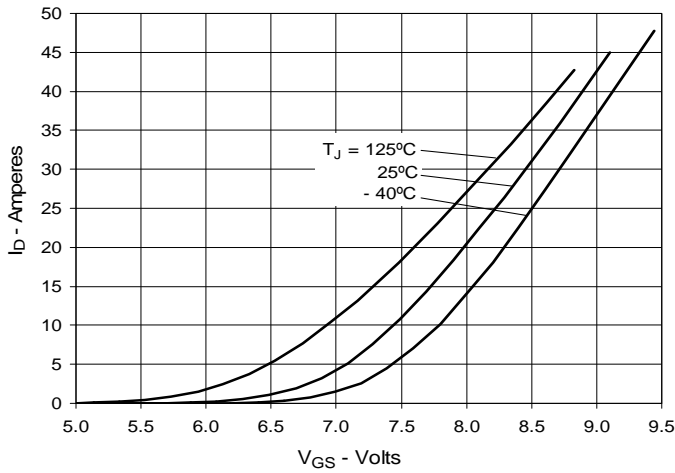


Fig. 8. Transconductance

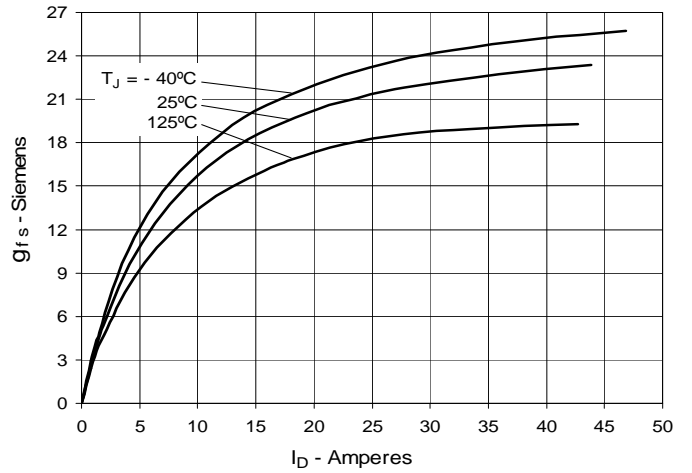


Fig. 9. Forward Voltage Drop of Intrinsic Diode

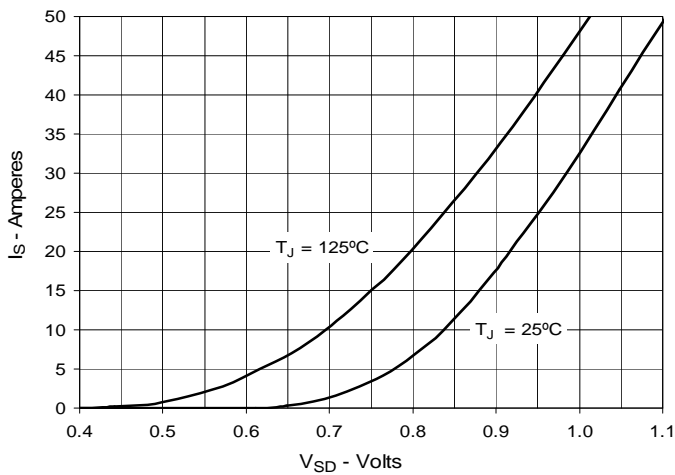


Fig. 10. Gate Charge

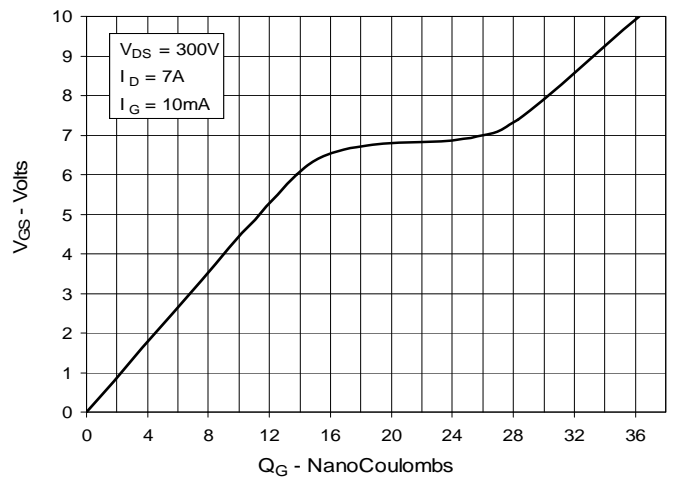


Fig. 11. Capacitance

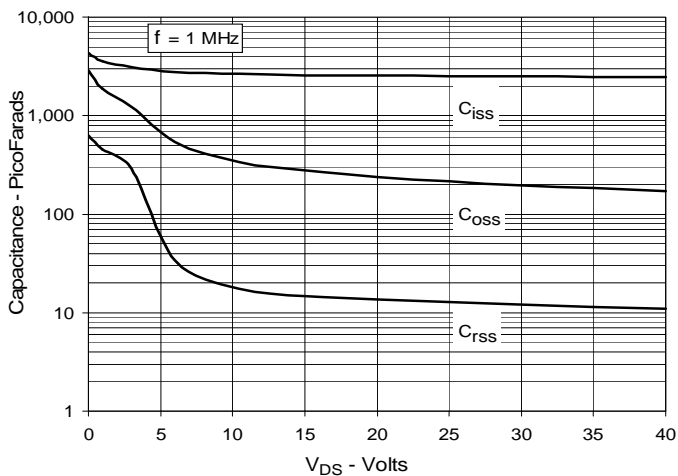


Fig. 12. Forward-Bias Safe Operating Area

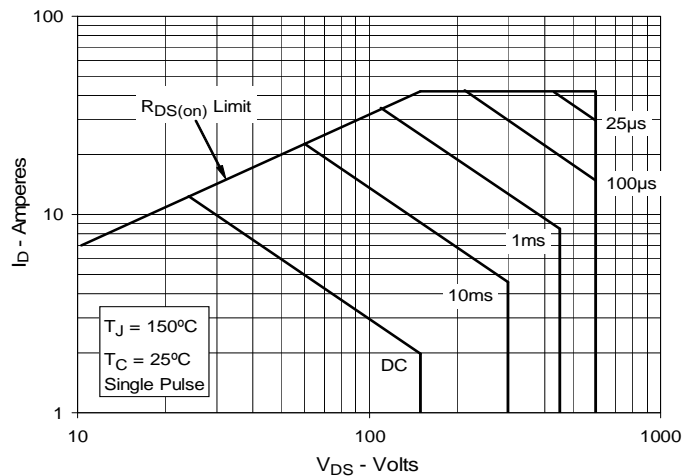


Fig. 13. Maximum Transient Thermal Impedance

